

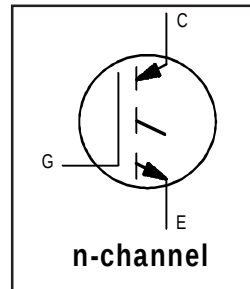
IRG4BC30S-S

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

Features

- Standard: optimized for minimum saturation voltage and low operating frequencies (< 1kHz)
- Generation 4 IGBT design provides tight parameter distribution and high efficiency



$V_{CES} = 600V$
 $V_{CE(on)} \text{ typ.} = 1.4V$
@ $V_{GE} = 15V, I_C = 18A$

Benefits

- Generation 4 IGBTs offer highest efficiency available
- IGBTs optimized for specified application conditions



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	34	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	18	
I_{CM}	Pulsed Collector Current ①	68	
I_{LM}	Clamped Inductive Load Current ②	68	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	10	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.2	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	1.44	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.75	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.40	1.6	V	$I_C = 18A$
		—	1.84	—		$I_C = 34A$
		—	1.45	—		$I_C = 18A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	6.0	11	—	S	$V_{CE} = 100V, I_C = 18A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	50	75	nC	$I_C = 18A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	7.3	11		$V_{CC} = 400V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	17	26		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	22	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 18A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 9, 10, 14
t_r	Rise Time	—	18	—		
$t_{d(off)}$	Turn-Off Delay Time	—	540	810		
t_f	Fall Time	—	390	590		
E_{on}	Turn-On Switching Loss	—	0.26	—	mJ	$T_J = 150^\circ\text{C}$, $I_C = 18A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 11, 14
E_{off}	Turn-Off Switching Loss	—	3.45	—		
E_{ts}	Total Switching Loss	—	3.71	5.6		
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 18A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 11, 14
t_r	Rise Time	—	19	—		
$t_{d(off)}$	Turn-Off Delay Time	—	790	—		
t_f	Fall Time	—	760	—		
E_{ts}	Total Switching Loss	—	6.55	—	mJ	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	1100	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	72	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	13	—		$f = 1.0MHz$

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature (See fig. 13b).
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu H$, $R_G = 23\Omega$, (See fig. 13a).
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

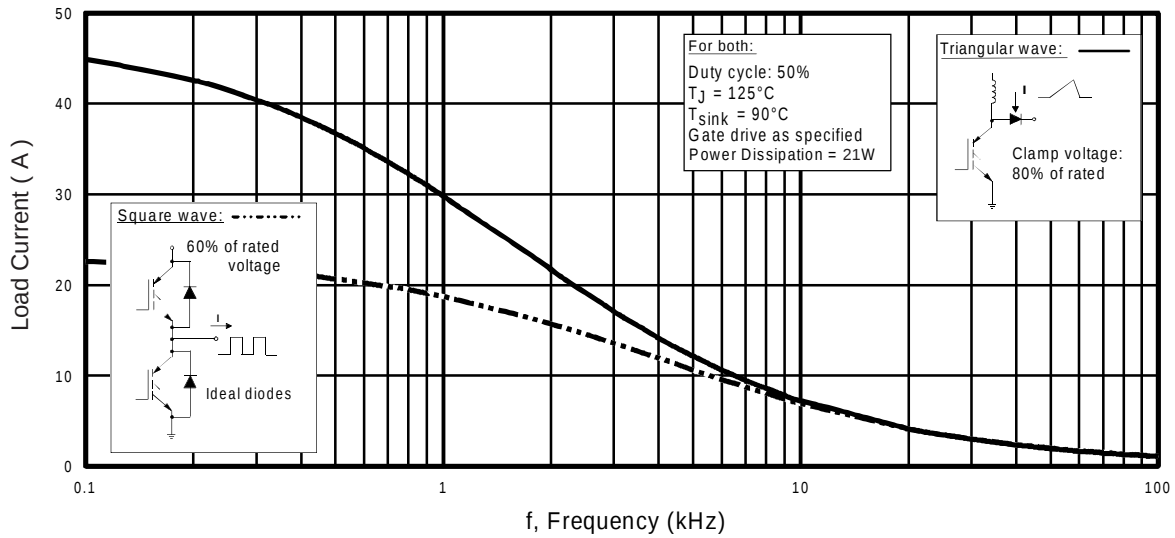


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

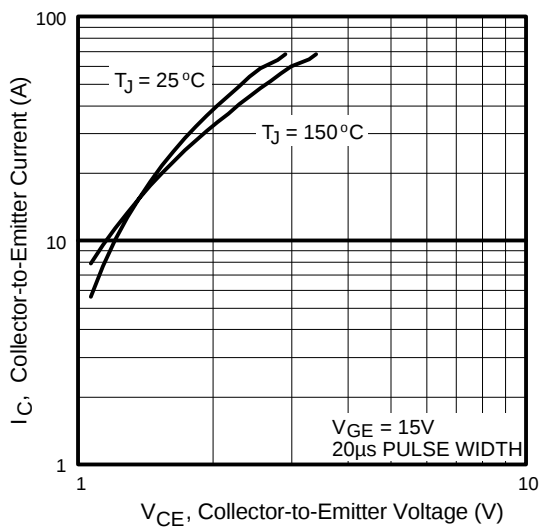


Fig. 2 - Typical Output Characteristics

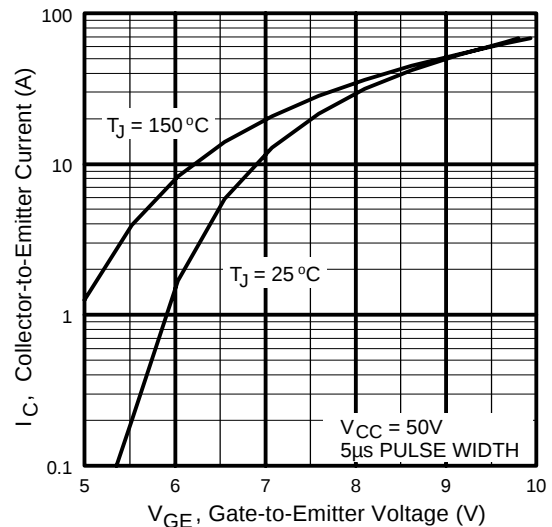


Fig. 3 - Typical Transfer Characteristics

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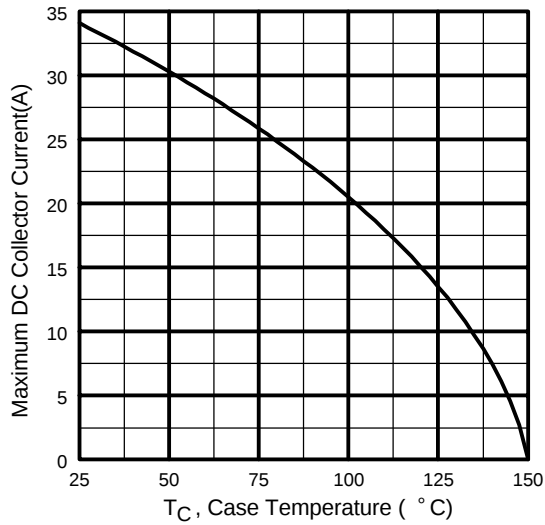


Fig. 4 - Maximum Collector Current vs. Case Temperature

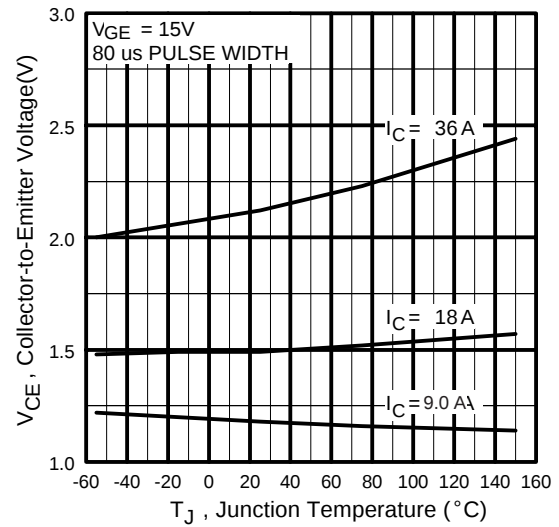


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

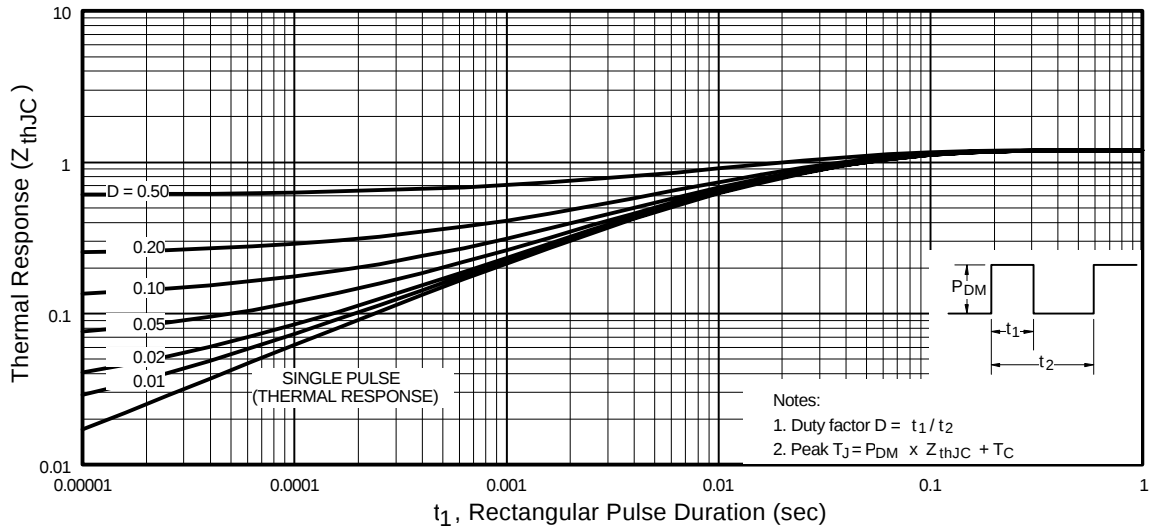
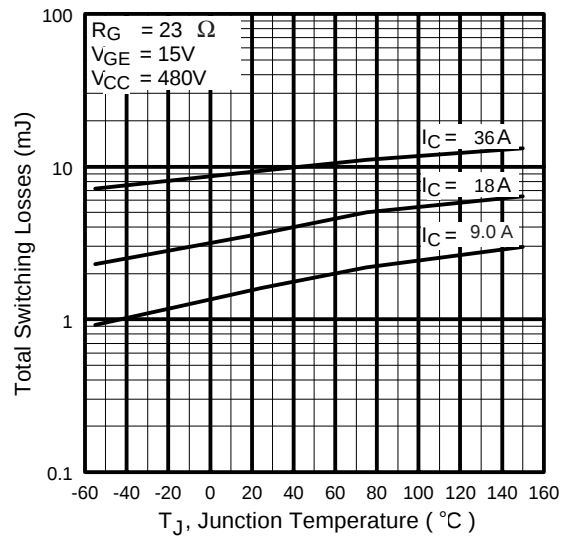
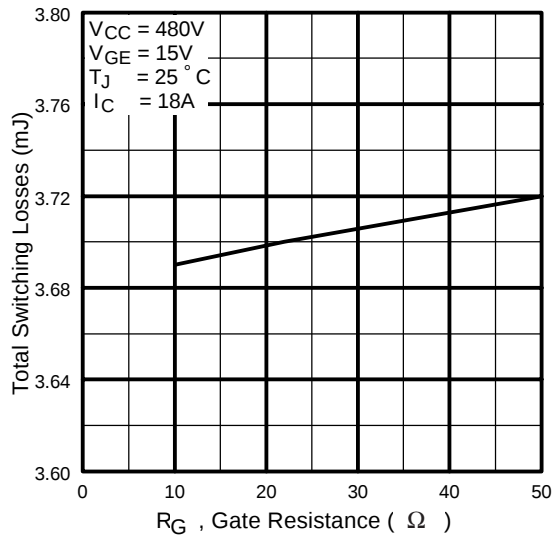
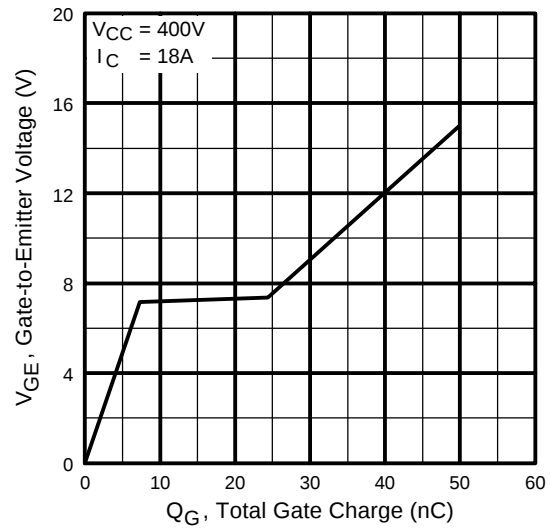
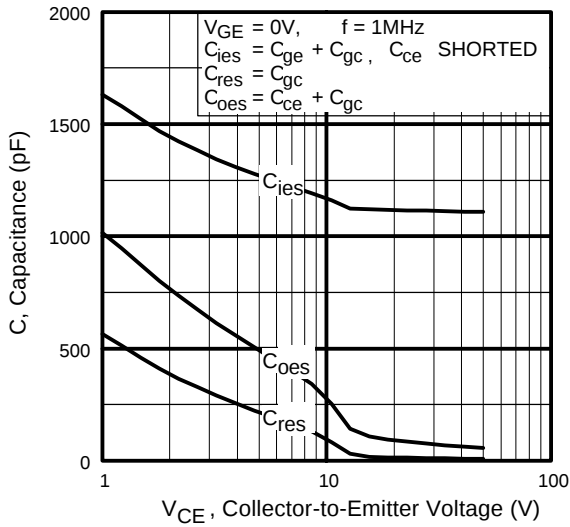


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



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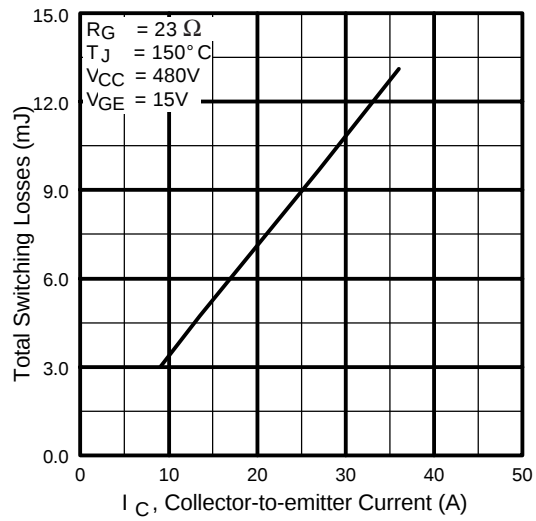


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

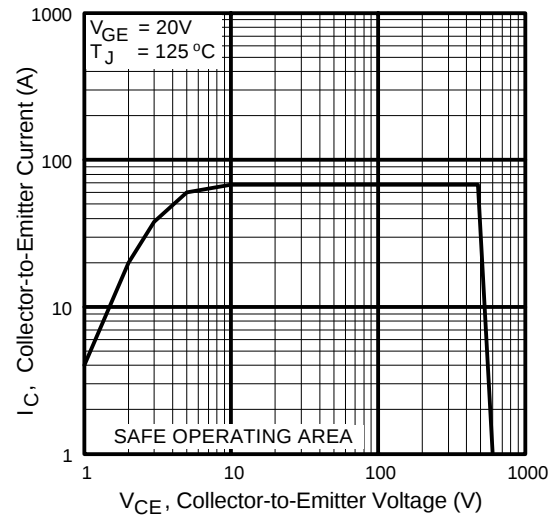


Fig. 12 - Turn-Off SOA

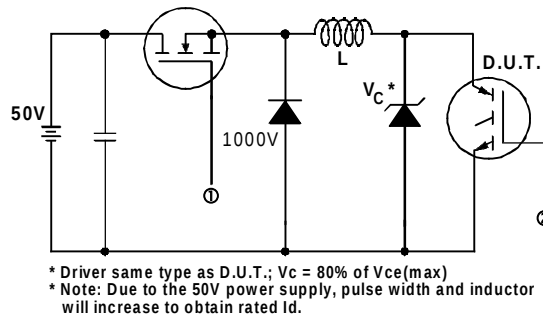


Fig. 13a - Clamped Inductive Load Test Circuit

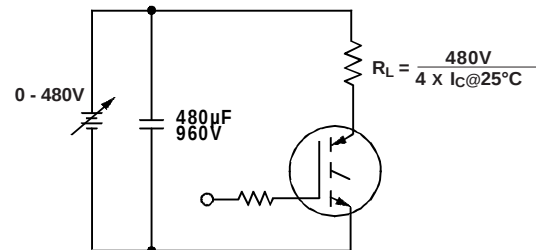


Fig. 13b - Pulsed Collector Current Test Circuit

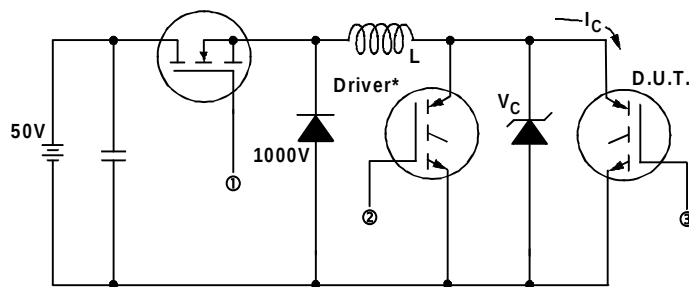


Fig. 14a - Switching Loss Test Circuit

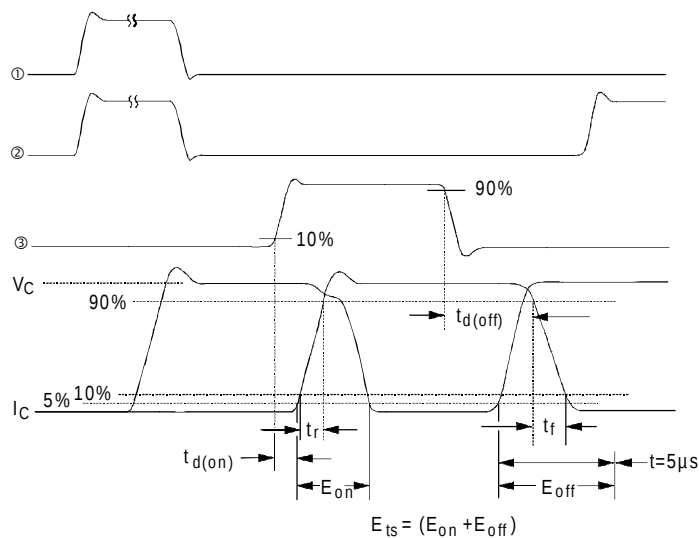
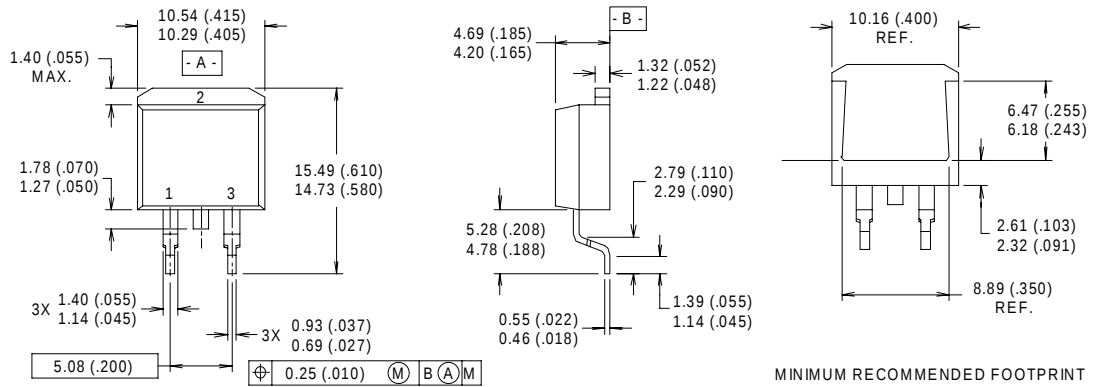


Fig. 14b - Switching Loss Waveforms

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D²Pak Package Outline



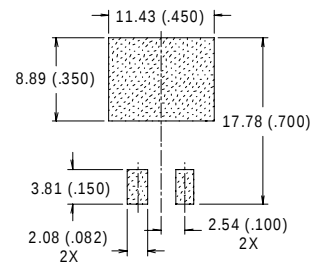
NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

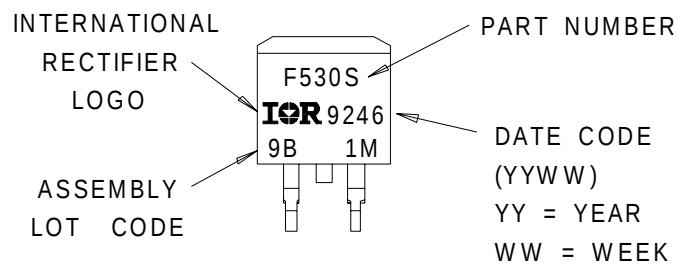
LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

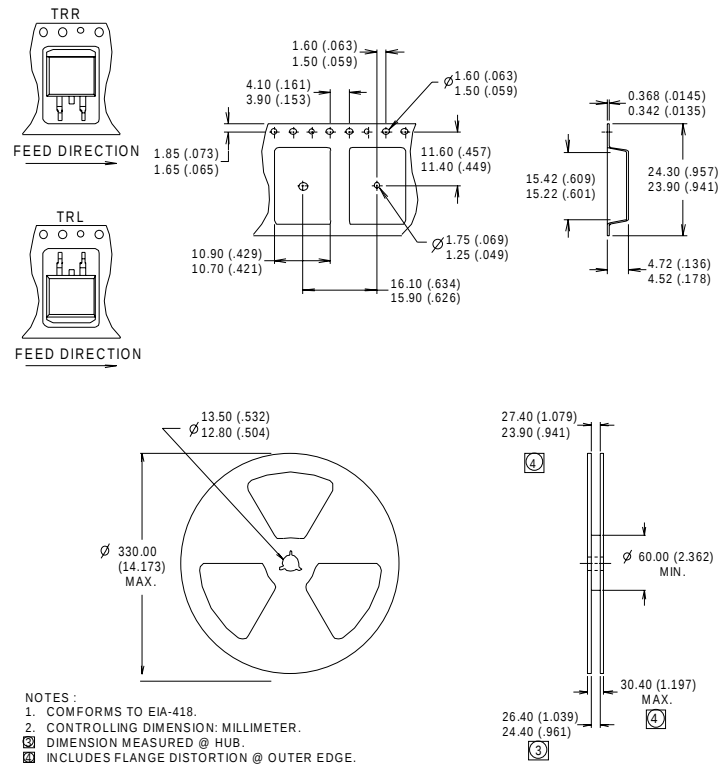
MINIMUM RECOMMENDED FOOTPRINT



D²Pak Part Marking Information



D²Pak Tape & Reel Information



Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>